

TITLE: A SILICIDED BURIED BITLINE PROCESS FOR A NON-VOLATILE MEMORY CELL INVENTOR(S): Daniel Sobek, Timothy J. Thurgate, Mark W. Randolph USSN: 09/885,426 Attorney Docket # AMD-E306

1/5

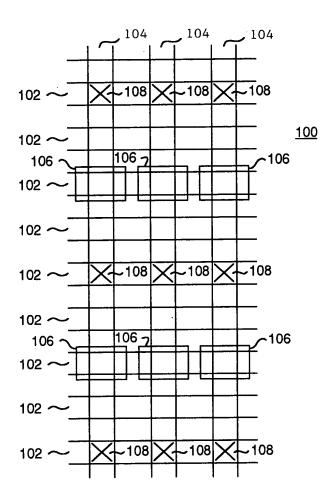


FIG. 1

PRIOR ART



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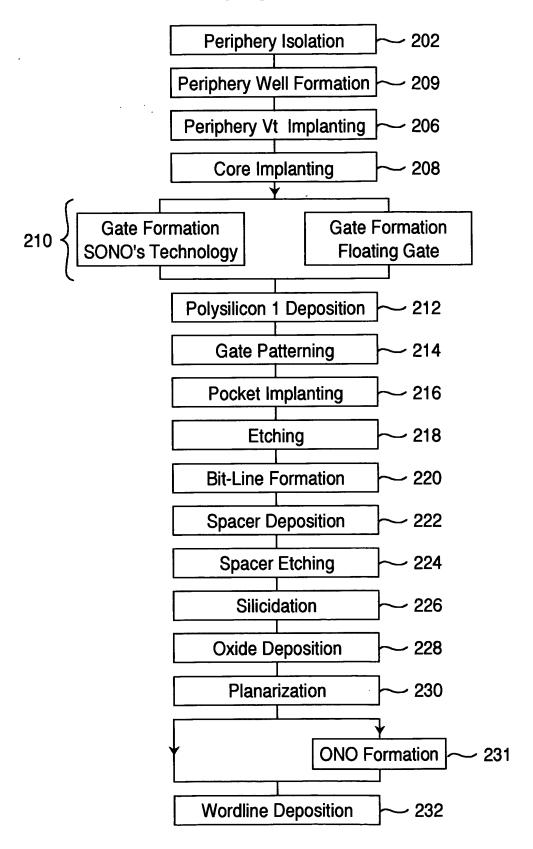


FIG. 2



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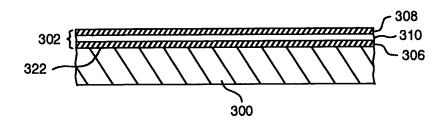


FIG. 3

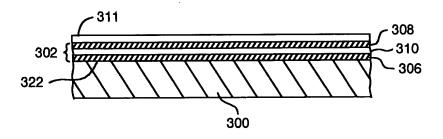


FIG. 4

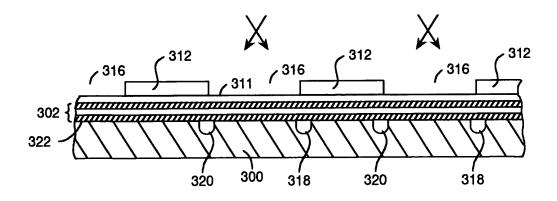


FIG. 5



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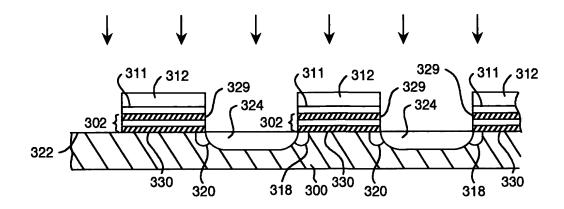


FIG. 6

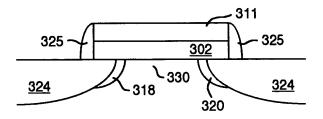


FIG. 7

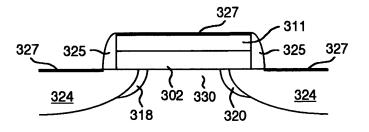


FIG. 8



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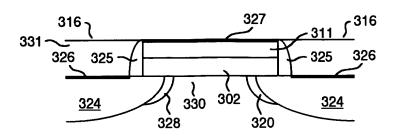


FIG. 9

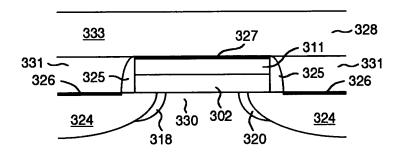


FIG. 10

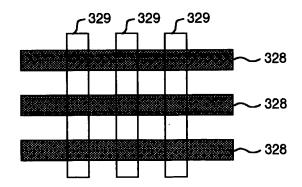


FIG. 11